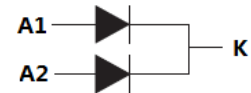
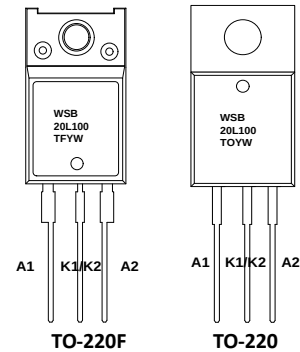


Power Schottky Barrier Rectifier
Features

- 2x10A average rectified forward current
- Low forward voltage and Low leakage current
- High Junction temperature
- High forward and reverse Surge capability

Applications

- High frequency switch model power supplies
- DC-DC Convertors, Power adapters

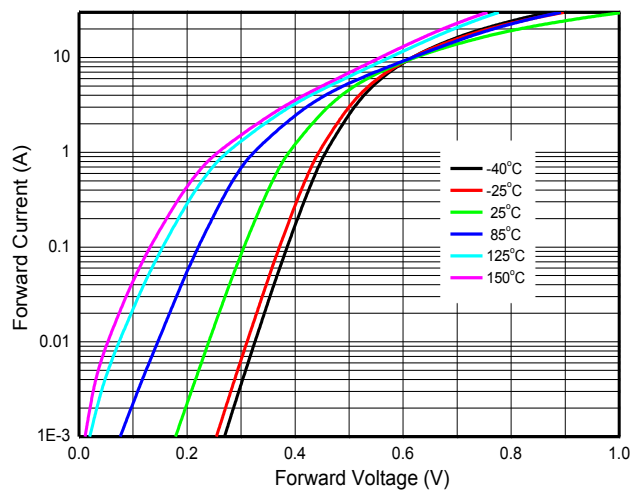
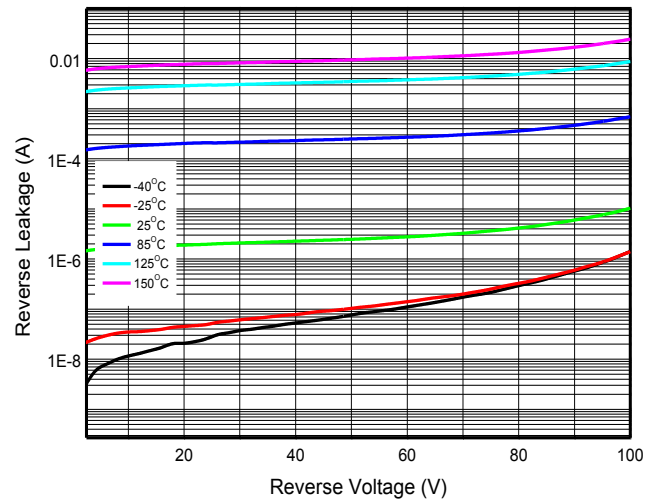
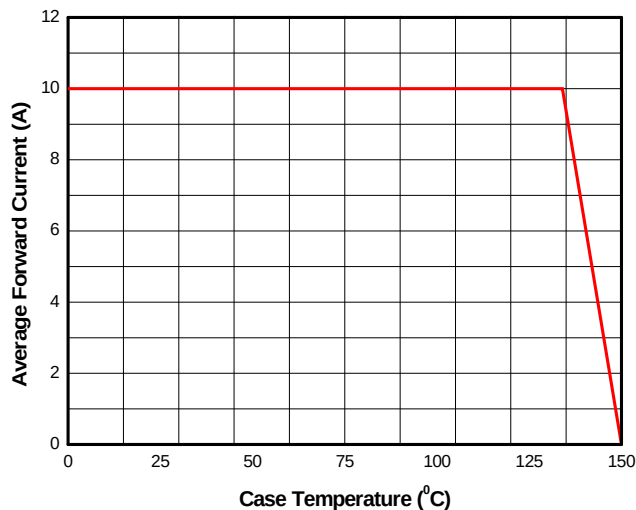
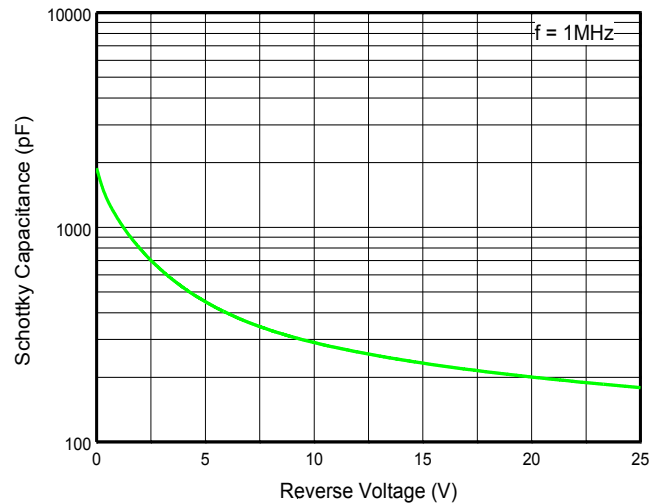

Circuit

WSB20L100 = Device code
TO/TF = Special code
Y =Year
W =Week (A~z)
Marking

Absolute maximum ratings				
Parameter		Symbol	Value	Unit
Reverse voltage (repetitive peak)		V_{RM}	100	V
Reverse voltage (DC)		V_R	100	V
Average rectified forward current	Per diode	I_F	10	A
	Per device	I_F	20	A
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave		I_{FSM}	200	A
Junction temperature		T_J	150	$^{\circ}C$
Operating temperature		T_{opr}	-55 ~ 150	$^{\circ}C$
Storage temperature		T_{stg}	-55 ~ 150	$^{\circ}C$
Thermal Resistance Ratings				
Maximum Thermal Resistance Junction To case (Per leg)	TO-220	$R_{\theta JC}$	2.0	$^{\circ}C/W$

Order information			
Device	Package	Marking	Units/Tube
WSB20L100T-3/T	TO-220	WSB20L100TOYW	50
WSB20L100TF-3/T	TO-220F	WSB20L100TFYW	50

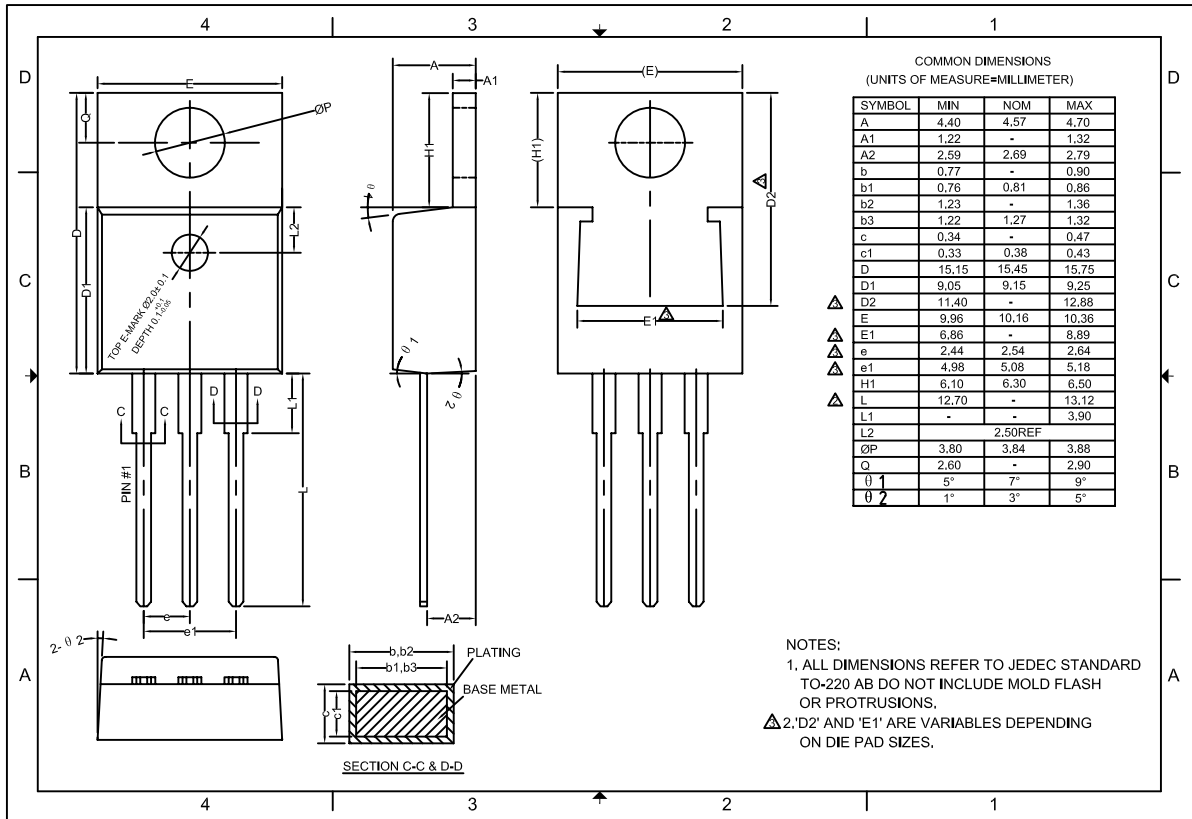
Electronics characteristics (Per diode, $T_A = 25^\circ\text{C}$)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage	V_R	$I_R=0.5\text{mA}$	100			V
Forward voltage	V_F	$I_F=10\text{A}$		0.6	0.7	V
Reverse current	I_R	$V_R=100\text{V}$	-	11	100	μA
Junction capacitance	C_J	$V_R=25\text{V}, F=1\text{MHz}$	-	180		pF

Typical characteristics ($T_A=25^\circ\text{C}$, unless otherwise noted)

Forward voltage vs. Forward current

Reverse current vs. Reverse voltage

Forward Current Derating Curve

Junction capacitance vs. Reverse voltage

Package outline dimensions

TO-220



TO-220F

